

MJE521G Datasheet



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DiGi Electronics Part Number MJE521G-DG

Manufacturer onsemi

Manufacturer Product Number MJE521G

Description TRANS NPN 40V 4A TO126

Detailed Description Bipolar (BJT) Transistor NPN 40 V 4 A 40 W Through

Hole TO-126



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DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MJE521G	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	4 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
40 V	
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100μA (ICBO)	40 @ 1A, 1V
Power - Max:	Frequency - Transition:
40 W	
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-225AA, TO-126-3	TO-126
Base Product Number:	
MJE521	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FΔRQQ	8541 29 0095

MJE521

Plastic Medium-Power NPN Silicon Transistor

These devices are designed for use in general-purpose amplifier and switching circuits. Recommended for use in 5 to 10 Watt audio amplifiers utilizing complementary symmetry circuitry.

Features

- DC Current Gain h_{FE} = 40 (Min) @ I_C = 1.0 Adc
- Complementary to PNP MJE371
- Pb-Free Package is Available*



Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V_{CB}	40	Vdc
Emitter Base Voltage	V _{EB}	4.0	Vdc
Collector Current – Continuous – Peak	I _C	4.0 8.0	Adc
Base Current – Continuous	I _B	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θЈС	3.12	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



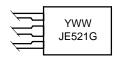
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4 AMPERES POWER TRANSISTORS NPN SILICON 40 VOLTS, 40 WATTS



MARKING DIAGRAM



Y = Year

WW = Work Week

JE521 = Device Code

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE521	TO-225	500 Units/Box
MJE521G	TO-225 (Pb-Free)	500 Units/Box

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJE521

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 100 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	40	-	Vdc
Collector–Base Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$	I _{CBO}	-	100	μAdc
Emitter-Base Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	-	100	μAdc
ON CHARACTERISTICS			_	
DC Current Gain (Note 1) (I _C = 1.0 Adc, V _{CE} = 1.0 Vdc)	h _{FE}	40	-	-

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MJE521

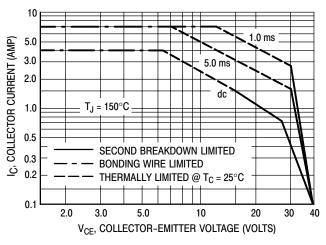


Figure 1. Active-Region Safe Operating Area

The data of Figure 1 based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $(T_{Jpk}) \le 150^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

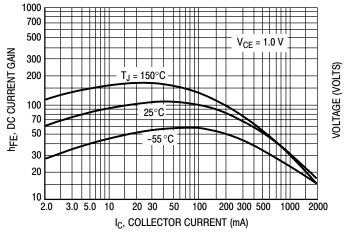


Figure 2. DC Current Gain

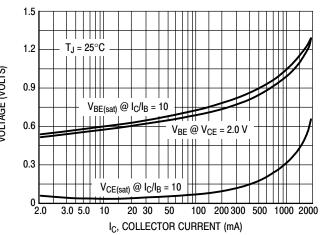


Figure 3. "On" Voltage

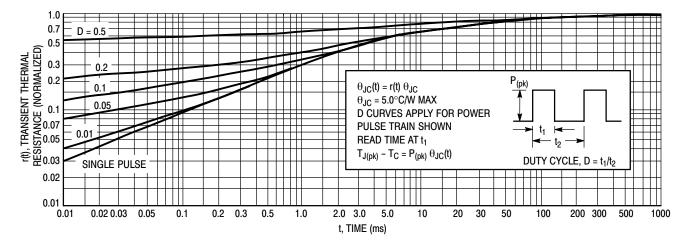
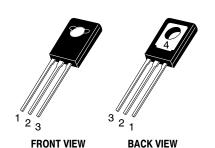


Figure 4. Thermal Response



MECHANICAL CASE OUTLINE

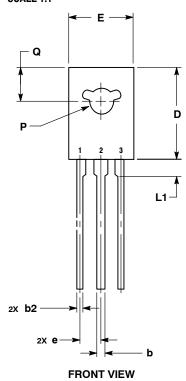
PACKAGE DIMENSIONS

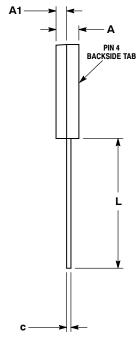


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1





SIDE VIEW

- NOTES:

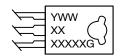
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.40	3.00		
A1	1.00	1.50		
b	0.60	0.90		
b2	0.51	0.88		
С	0.39	0.63		
D	10.60	11.10		
E	7.40	7.80		
е	2.04	2.54		
L	14.50	16.63		
L1	1.27	2.54		
P	2.90	3.30		
Q	3.80	4.20		

GENERIC MARKING DIAGRAM*



= Year ww = Work Week XXXXX = Device Code = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. 2., 4. 3.	EMITTER COLLECTOR BASE	STYLE 2: PIN 1. 2., 4. 3.	STYLE 3: PIN 1. 2., 4. 3.	BASE COLLECTOR EMITTER	STYLE 4: PIN 1. 2., 4. 3.	ANODE 1 ANODE 2 GATE	2., 4.	MT 1 MT 2 GATE
STYLE 6: PIN 1. 2., 4. 3.	CATHODE GATE ANODE	STYLE 7: PIN 1. 2., 4. 3.	STYLE 8: PIN 1. 2., 4. 3.	SOURCE GATE DRAIN	STYLE 9: PIN 1. 2., 4. 3.	GATE DRAIN SOURCE	STYLE 10: PIN 1. 2., 4. 3.	SOURCE DRAIN

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DESCRIPTION:	TO-225		PAGE 1 OF 1	

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